

N-Channel Enhancement Mode Power MOSFET

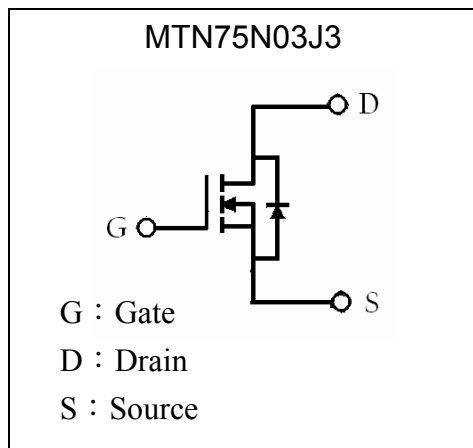
MTN75N03J3

BV_{DSS}	25V
I_D	75A
R_{DSON}	4.5m Ω

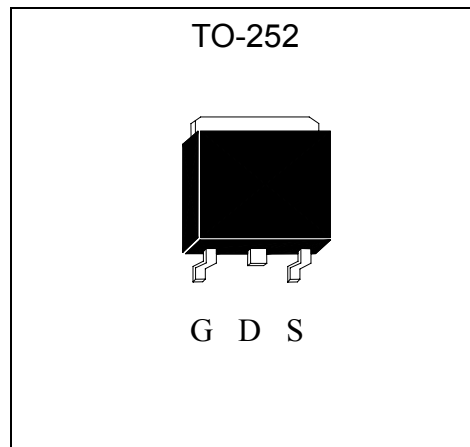
Features

- Low Gate Charge
- Simple Drive Requirement
- Repetitive Avalanche Rated
- Fast Switching Characteristic
- RoHS compliant package

Symbol



Outline



Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current @ $V_{GS}=4.5V, T_c=25^\circ C$	I_D	75	A
Continuous Drain Current @ $V_{GS}=4.5V, T_c=100^\circ C$	I_D	62.5	A
Pulsed Drain Current	I_{DM}	350 *1	A
Total Power Dissipation ($T_c=25^\circ C$)	P_d	96	W
Linear Derating Factor		0.75	W/ $^\circ C$
Single Pulse Avalanche Energy	E_{AS}	400 *2	mJ
Single Pulse Avalanche Current	I_{AS}	40	A
Operating Junction and Storage Temperature	T_j, T_{stg}	-55~+150	$^\circ C$

Note : *1. Pulse width limited by safe operating area

*2. $T_j=25^\circ C, V_{DD}=20V, L=0.1mH, R_G=25\Omega, I_{AS}=10A$



Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	1.3	°C/W
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	110	°C/W

Characteristics (Tj=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	25	-	-	V	$V_{GS}=0, I_D=250\mu A$
$\Delta BV_{DSS}/\Delta T_j$	-	0.02	-	V/°C	Reference to 25°C, $I_D=1mA$
$V_{GS(th)}$	1.0	-	3.0	V	$V_{DS} = V_{GS}, I_D=250\mu A$
G_{FS}	-	29	-	S	$V_{DS} = 10V, I_D=30A$
I_{GSS}	-	-	±100	nA	$V_{GS}=\pm 20$
I_{DSS}	-	-	1	μA	$V_{DS} = 25V, V_{GS} = 0$
I_{DSS}	-	-	25	μA	$V_{DS} = 20V, V_{GS} = 0, T_j=150^\circ C$
* $R_{DS(ON)}$	-	3.7	4.5	mΩ	$V_{GS} = 10V, I_D=40A$
* $R_{DS(ON)}$	-	6.0	7	mΩ	$V_{GS} = 4.5V, I_D=30A$
Dynamic					
* Q_g	-	33	-	nC	$I_D=30A, V_{DS}=20V, V_{GS}=4.5V$
* Q_{gs}	-	9	-		
* Q_{gd}	-	15	-		
* $t_{d(ON)}$	-	10	-	ns	$V_{DS}=15V, I_D=30A, V_{GS}=10V,$ $R_G=3.3\Omega, R_D=0.5\Omega$
* t_r	-	80	-		
* $t_{d(OFF)}$	-	37	-		
* t_f	-	85	-		
C_{iss}	-	2070	-	pF	$V_{GS}=0V, V_{DS}=25V, f=1MHz$
C_{oss}	-	990	-		
C_{rss}	-	300	-		
Source-Drain Diode					
* V_{SD}	-	-	1.5	V	$I_S=20A, V_{GS}=0V$
* t_{rr}	-	50	-	ns	$I_S=30A, V_{GS}=0, dI/dt=100A/\mu s$
* Q_{rr}	-	51	-	nC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycles ≤2%

Ordering Information

Device	Package	Shipping	Marking
MTN75N03J3	TO-252 (RoHS compliant)	2500 pcs / Tape & Reel	75N03

Characteristic Curves

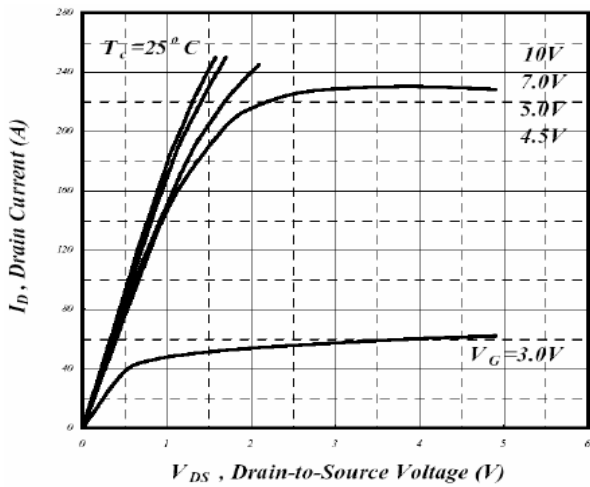


Fig 1. Typical Output Characteristics

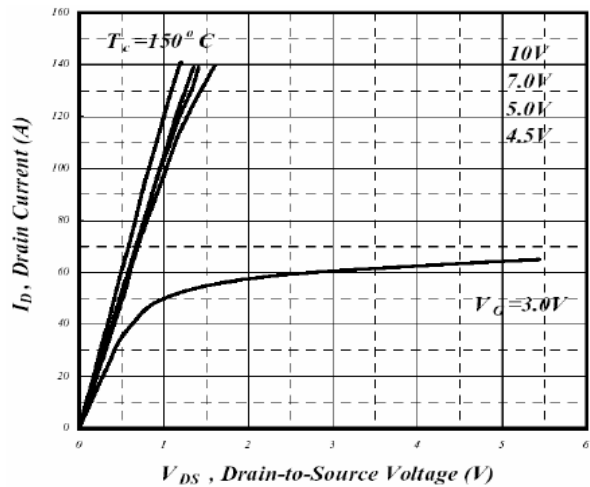


Fig 2. Typical Output Characteristics

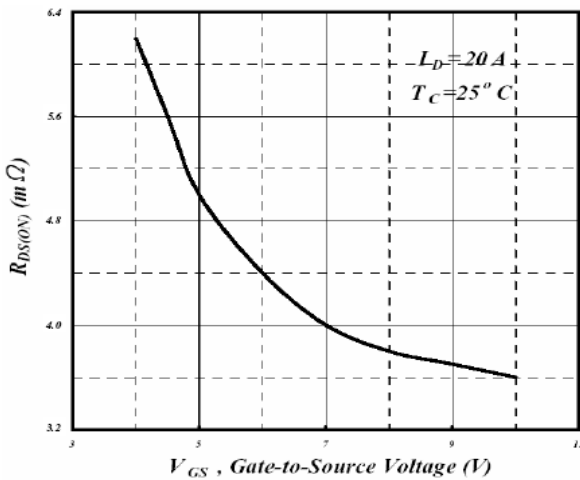


Fig 3. On-Resistance v.s. Gate Voltage

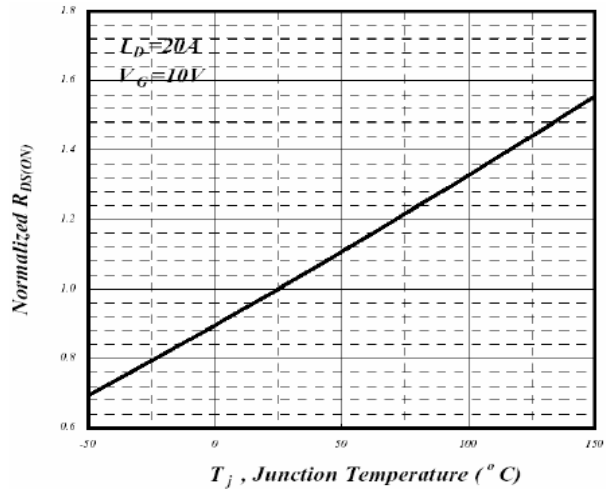


Fig 4. Normalized On-Resistance v.s. Junction Temperature

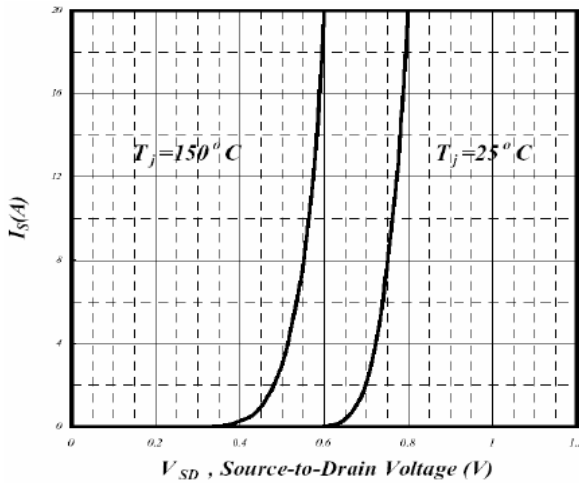


Fig 5. Forward Characteristics of Reverse Diode

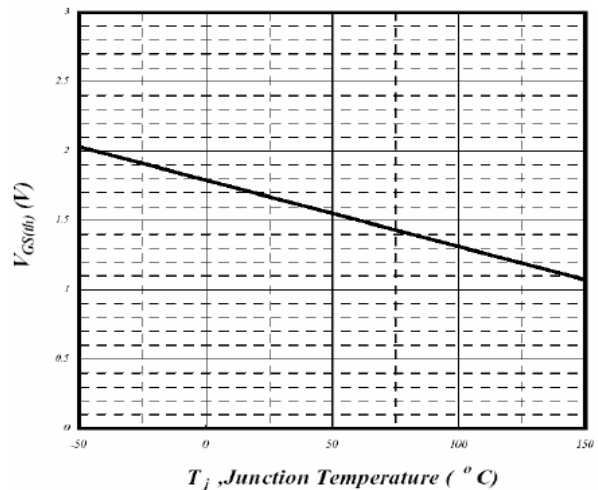


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

Characteristic Curves(Cont.)

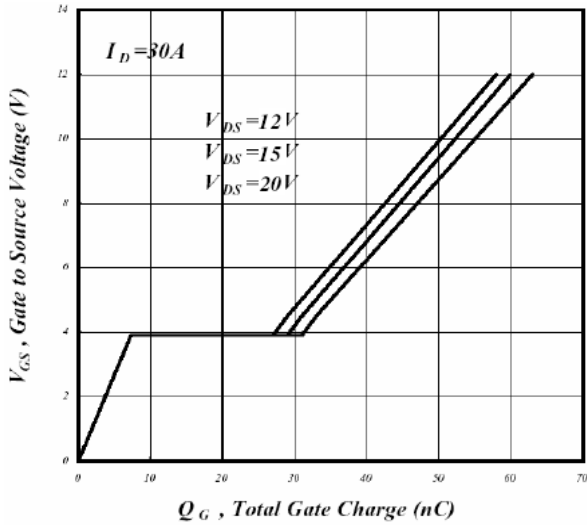


Fig 7. Gate Charge Characteristics

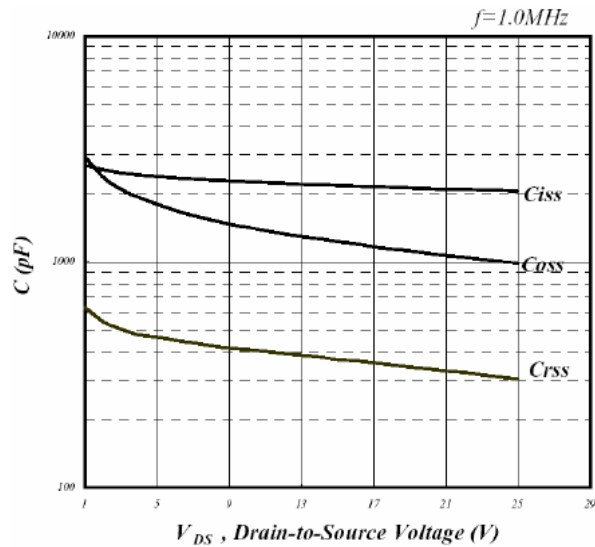


Fig 8. Typical Capacitance Characteristics

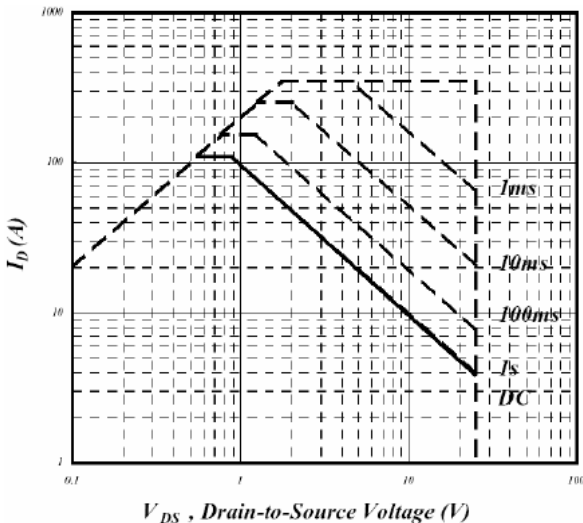


Fig 9. Maximum Safe Operating Area

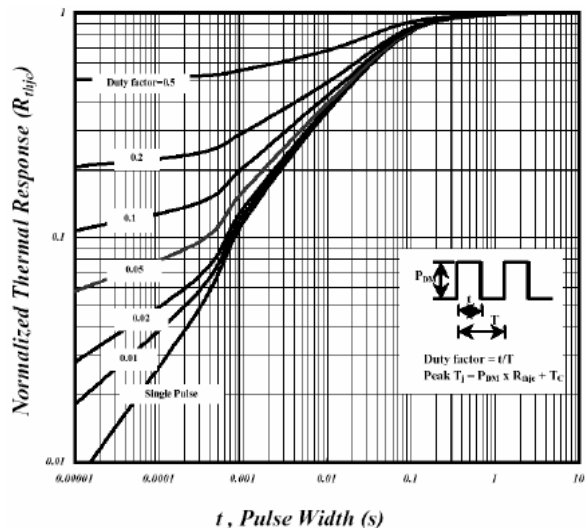


Fig 10. Effective Transient Thermal Impedance

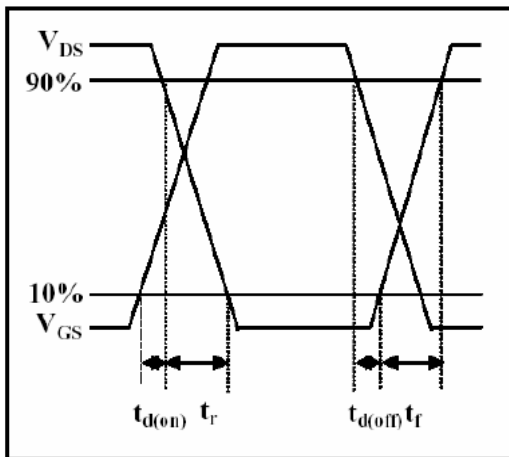


Fig 11. Switching Time Waveform

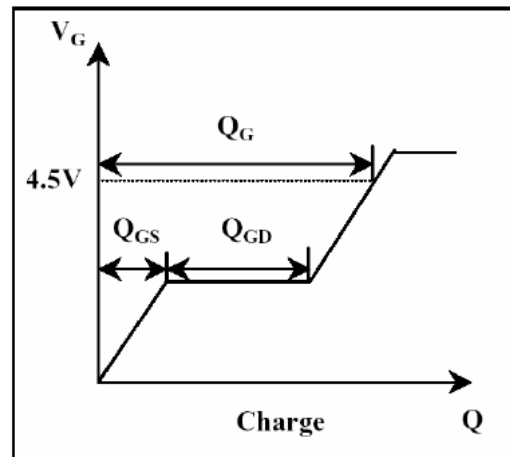
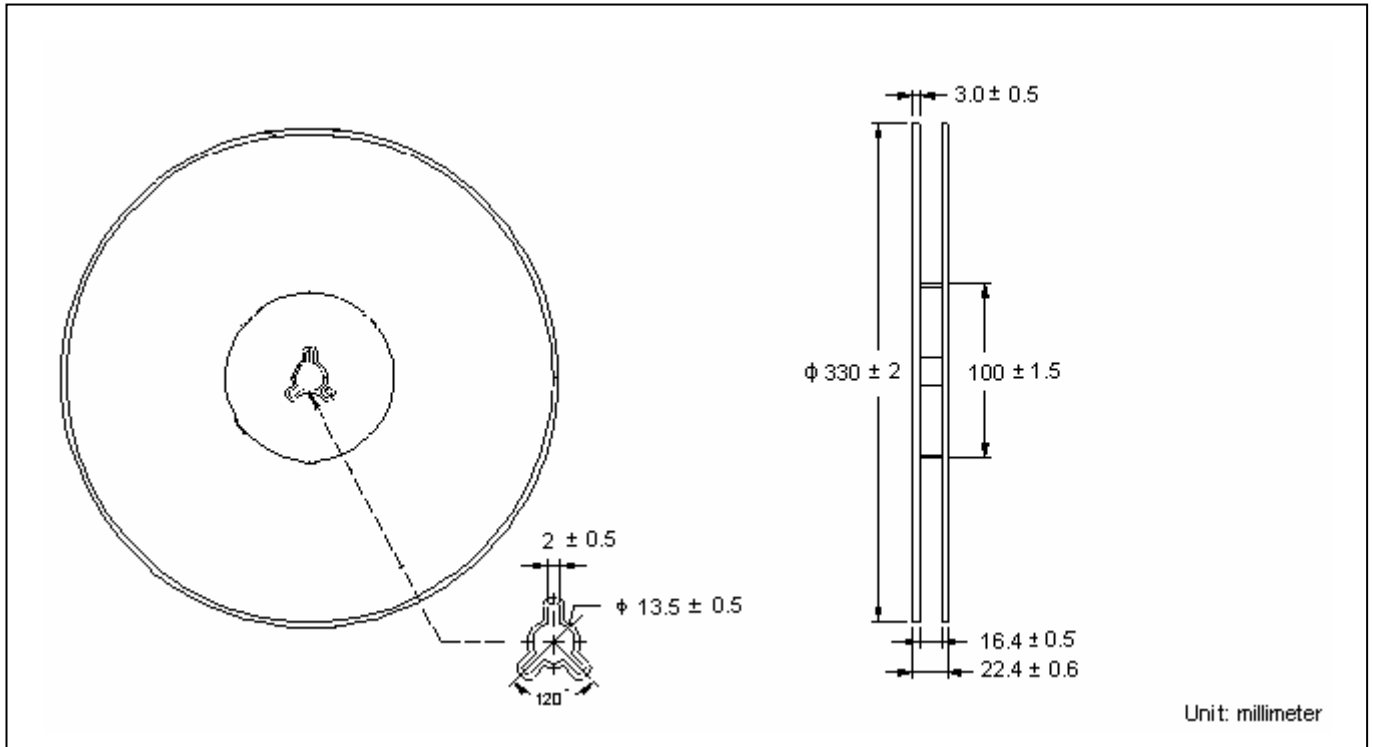
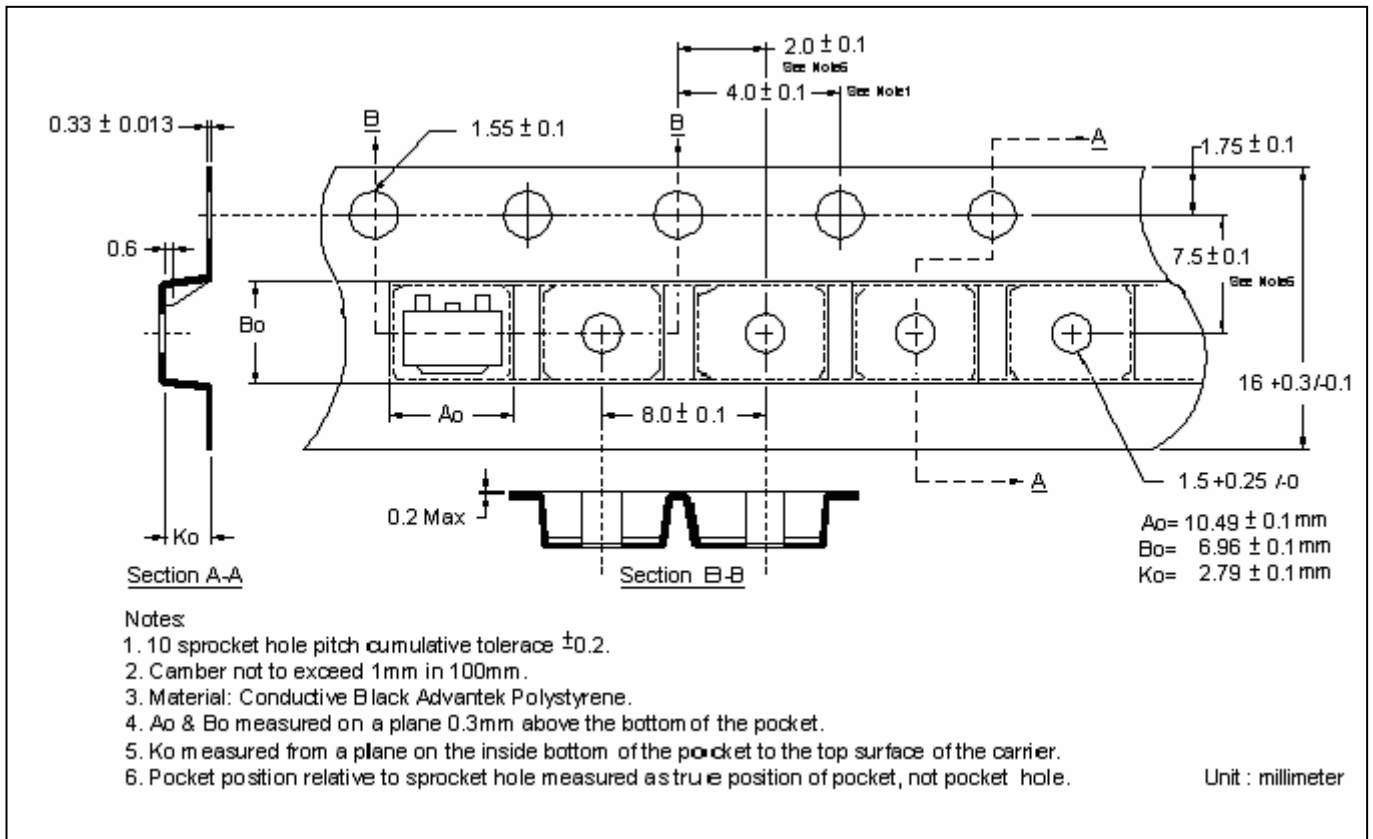


Fig 12. Gate Charge Waveform

Reel Dimension

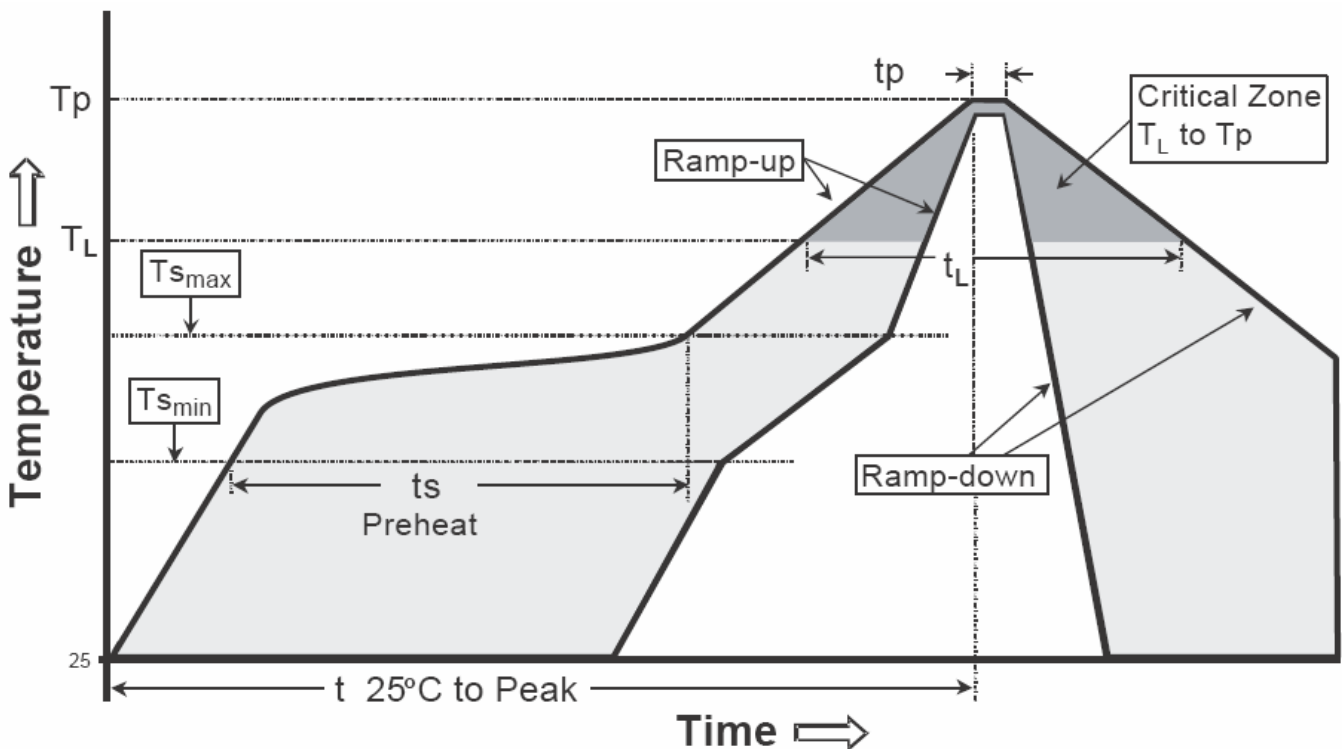


Carrier Tape Dimension



Recommended wave soldering condition

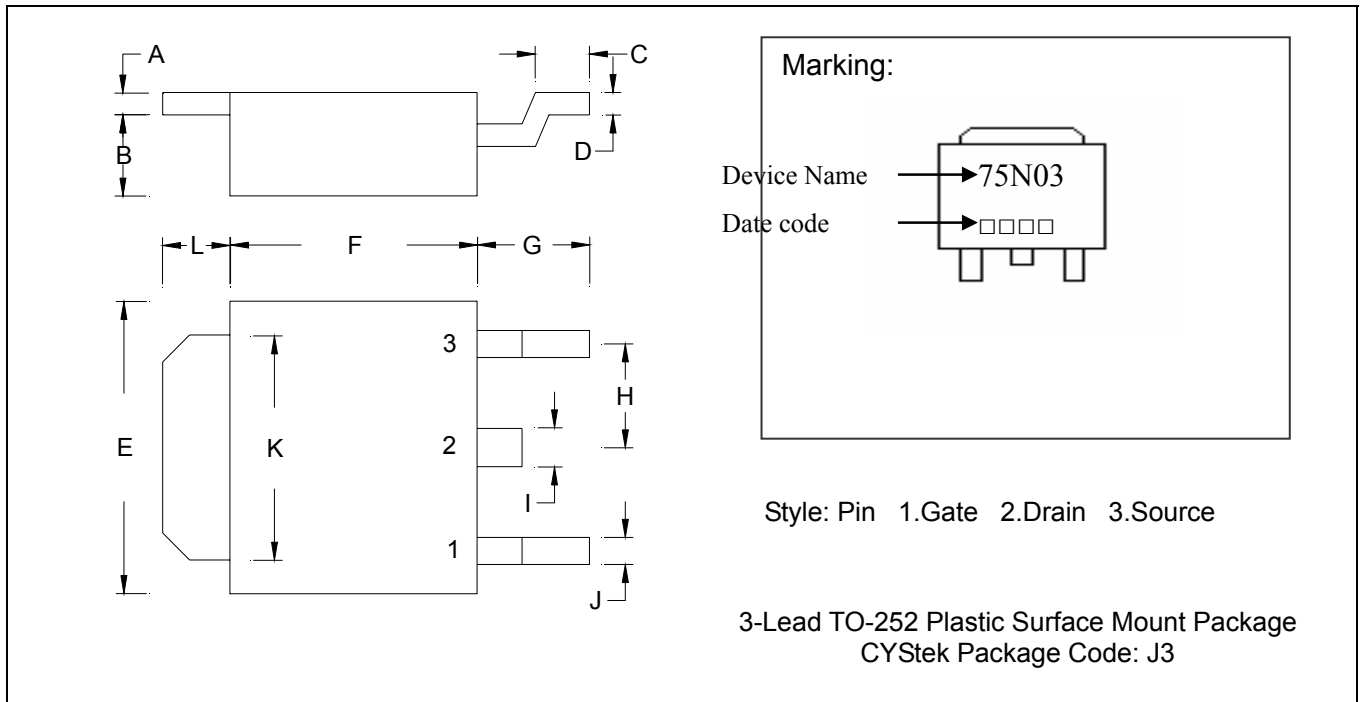
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-252 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0177	0.0217	0.45	0.55	G	0.0866	0.1102	2.20	2.80
B	0.0650	0.0768	1.65	1.95	H	-	*0.0906	-	*2.30
C	0.0354	0.0591	0.90	1.50	I	-	0.0449	-	1.14
D	0.0177	0.0236	0.45	0.60	J	-	0.0346	-	0.88
E	0.2441	0.2677	6.20	6.80	K	0.2047	0.2165	5.20	5.50
F	0.2125	0.2283	5.40	5.80	L	0.0551	0.0630	1.40	1.60

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: KFC; pure tin plated
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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